



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	5.2m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	8m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Power switching application
Uninterruptible power supply
DC-DC convertor

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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YJG85G06B

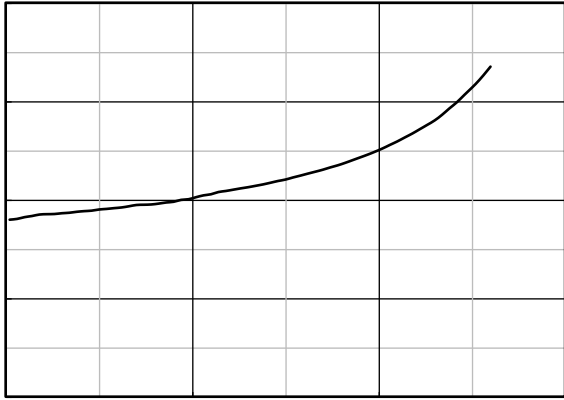


Figure 7. $R_{DS(on)}$ VS Drain Current

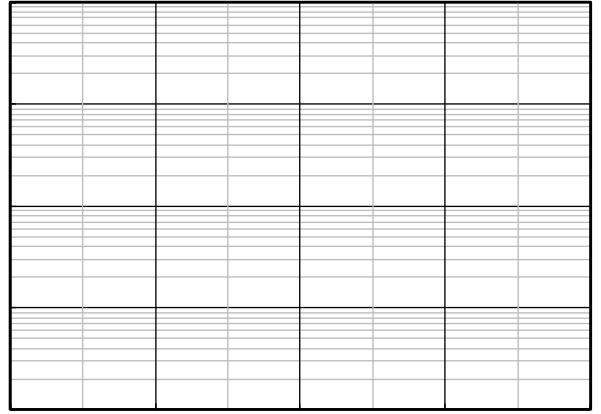


Figure 8. Forward characteristics of reverse diode

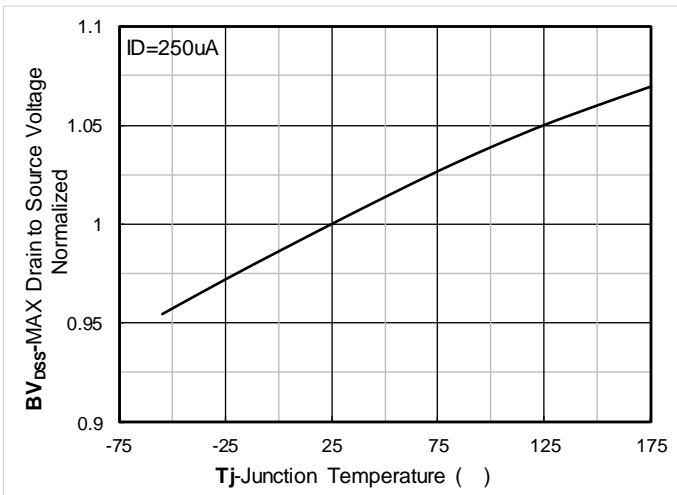


Figure 9. Normalized breakdown voltage

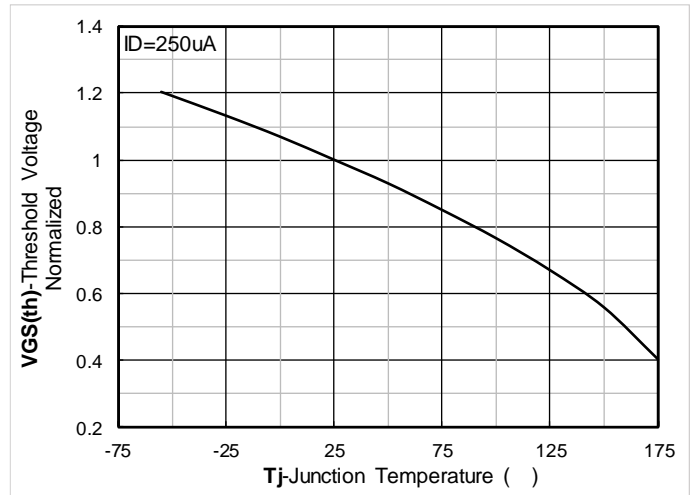


Figure 10. Normalized Threshold voltage

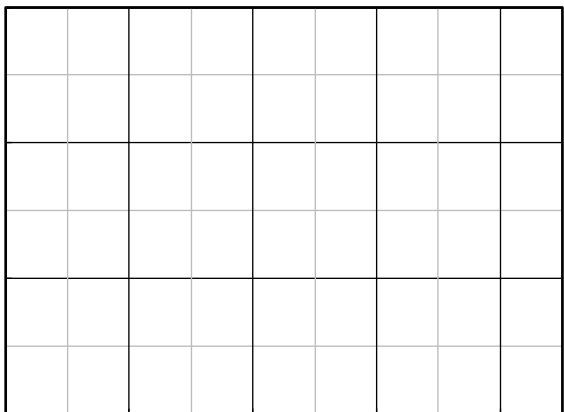


Figure 11. Current dissipation

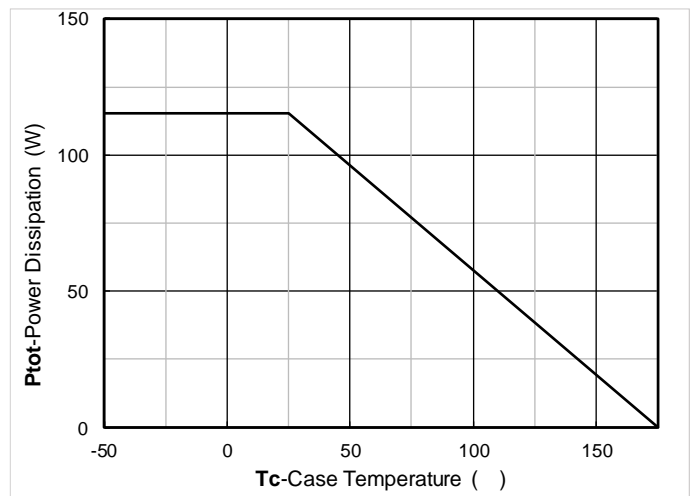


Figure 12. Power dissipation

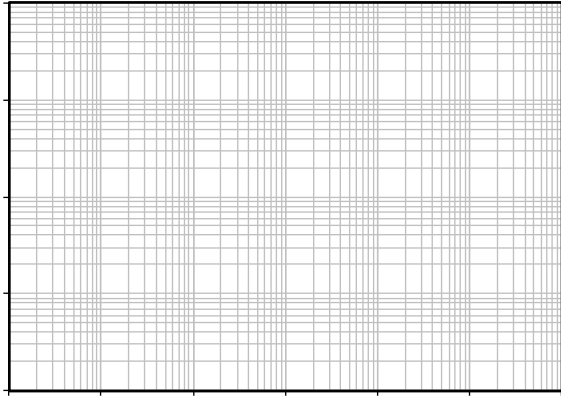


Figure 13. Maximum Transient Thermal Impedance

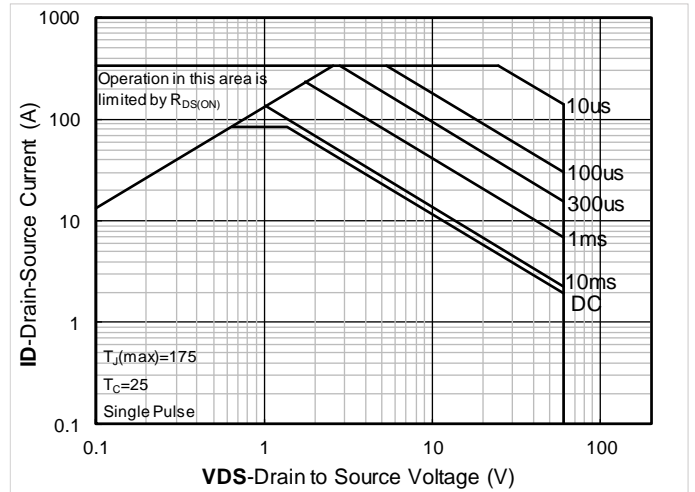


Figure 14. Safe Operation Area

Test Circuits & Waveforms

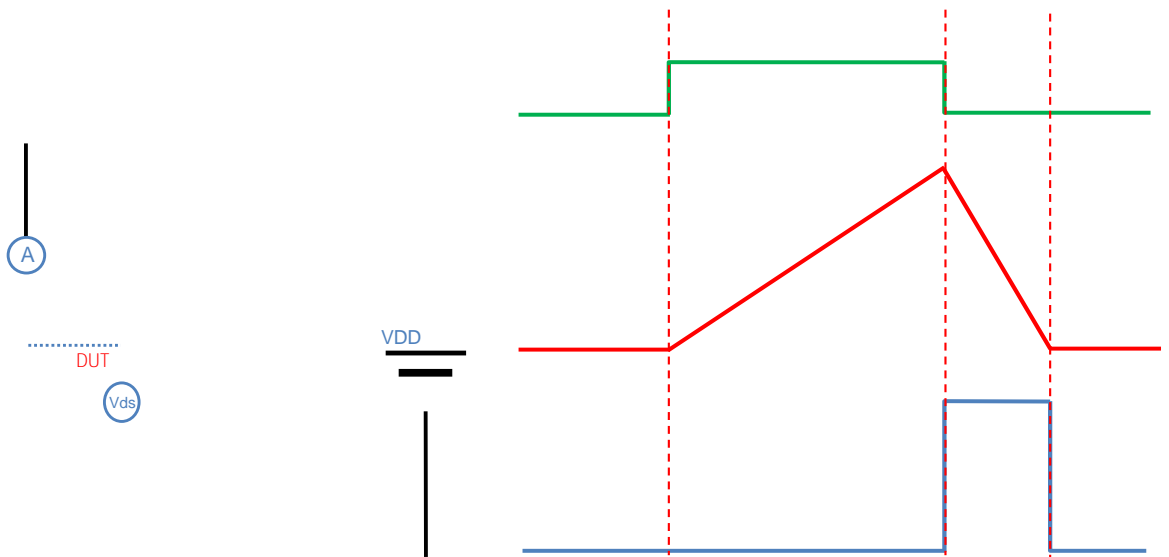


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

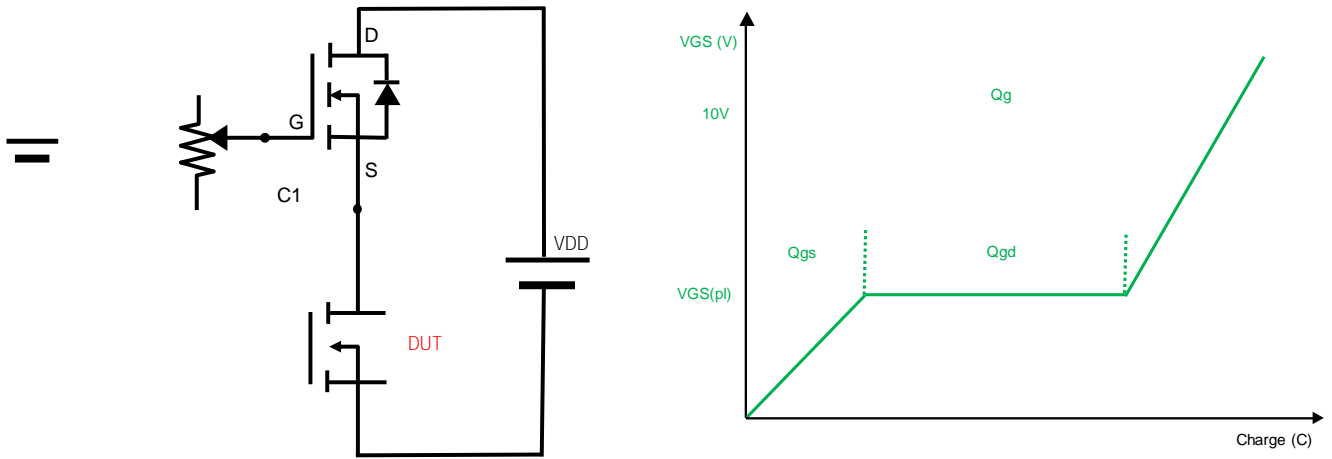


Figure B. Gate Charge Test Circuit & Waveform

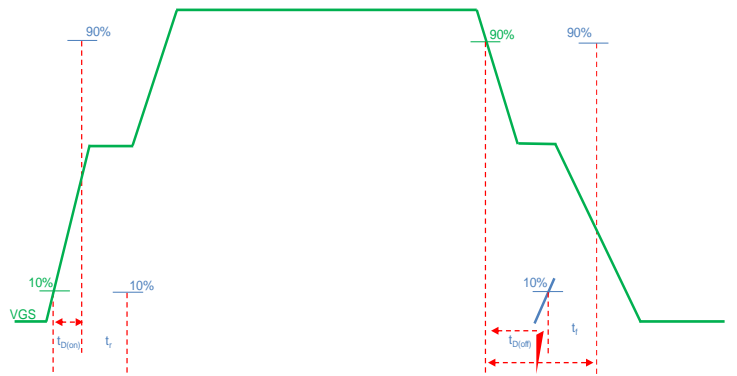


Figure C. Resistive Switching Test Circuit & Waveform

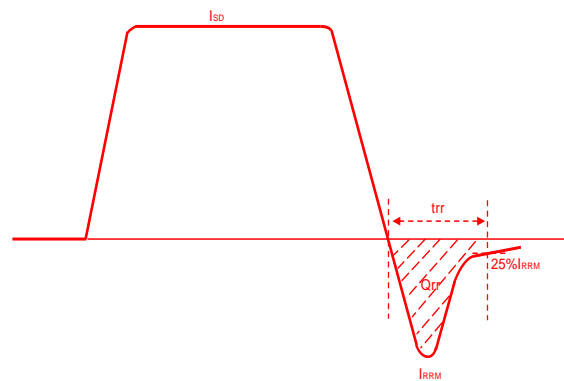


Figure D. Diode Recovery Test Circuit & Waveform



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Disc 59.84.2eWsB2eW*nBT/F5 0 g0 G(1)JTJETQq.00000888